

N-channel 80 V, 3 mΩ standard level FET in D2PAK Rev. 2 — 29 February 2012 Production

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in D2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switch

- Motor control
- Server power supplies

1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	80	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	<u>[1]</u>	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	306	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>		-	4.21	5	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u>		-	2.55	3	mΩ
Dynamic	characteristics						
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I_{D} = 75 A; V_{DS} = 40 V;		-	27	-	nC
Q _{G(tot)}	total gate charge	see <u>Figure 14</u> ; see <u>Figure 15</u>		-	139	-	nC
Avalanch	e ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; \text{T}_{j(\text{init})} = 25 \text{ °C}; \text{I}_\text{D} = 120 \text{ A}; \\ V_{sup} \leq 80 \text{ V}; \text{R}_{GS} = 50 \Omega; \text{ unclamped} $		-	-	676	mJ

[1] Continuous current is limited by package.

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	drain	i3	
				mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R8-80BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

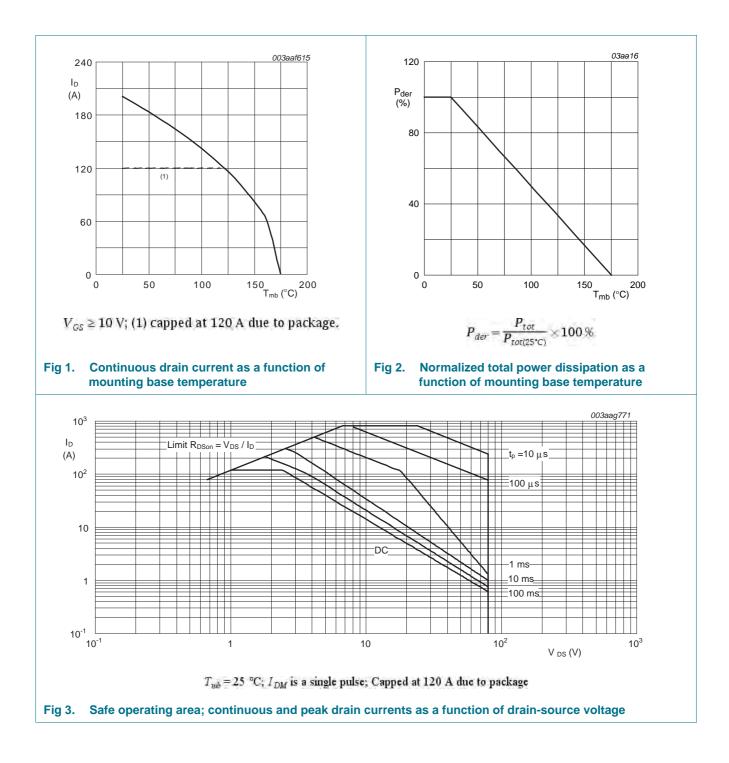
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	80	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u> -	120	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u> -	120	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	824	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	306	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drain	n diode				
I _S	source current	T _{mb} = 25 °C	<u>[1]</u> -	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	824	А
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω; unclamped	-	676	mJ

[1] Continuous current is limited by package.

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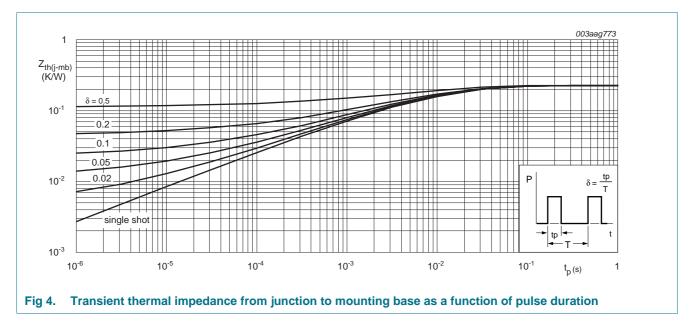
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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	0.22	0.49	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W



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Characteristics 6.

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	73	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	80	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 10	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
I _{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	10	μA
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
R _{DSon} drain-source on-star resistance	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	6.12	7.2	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see Figure 12; see Figure 13	-	4.21	5	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u>	-	2.55	3	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}$	-	135	-	nC
		$I_D = 75 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	139	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	51	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	30	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	21	-	nC
Q _{GD}	gate-drain charge		-	27	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 75 \text{ A}; V_{DS} = 40 \text{ V}; \text{see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	5.8	-	V
C _{iss}	input capacitance	V _{DS} = 40 V; V _{GS} = 0 V; f = 1 MHz;	-	9961	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	847	-	pF
C _{rss}	reverse transfer capacitance		-	401	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 0.53 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	41	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; \ I_D = 75 \ A$	-	43	-	ns
t _{d(off)}	turn-off delay time		-	109	-	ns
t _f	fall time		-	44	-	ns

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Symbol

Source-drain diode

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Тур

Max

Unit

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Min

	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V};$ see <u>Figure 17</u>	T _j = 25 °C;	-	0.8	1.2	V
r	reverse recovery time	$I_{\rm S} = 25 \text{ A}; \text{ d}I_{\rm S}/\text{d}t = 10$	0 A/µs; V _{GS} = 0 V;	-	63	-	ns
) _r	recovered charge	V _{DS} = 20 V		-	121	-	nC
250 g _{fs} (S) 200		003aaf602	75 I _D (A)			003aaf603	
150			50				
50			25	T _j = 175 °C		= 25 ∘C	
0 0	20 40	60 80 I _D (A)	0 0	2	/ 4 _{V_G}	6	
	$T_j = 25 ^{\circ}C; V_{DS} = 25$			$V_{DS} > I_D \times R$			
	ward transconductance a						
drai	in current; typical values	as a function of	Fig 6. Transfer cha function of g	aracteristics gate-source			
drai 16000 C (pF) 12000					voltage		
16000 C (pF)		003aaf606	function of g	gate-source	voltage	; typical	
16000 C (pF) 12000		003aaf606 C _{iss}	function of g	gate-source	Voltage	2003aad685 4.5	
16000 C (pF) 12000 8000 4000	in current; typical values	003aaf606	function of g	gate-source	Voltage	() = 4	

Table 6. Characteristics ...continued

Parameter

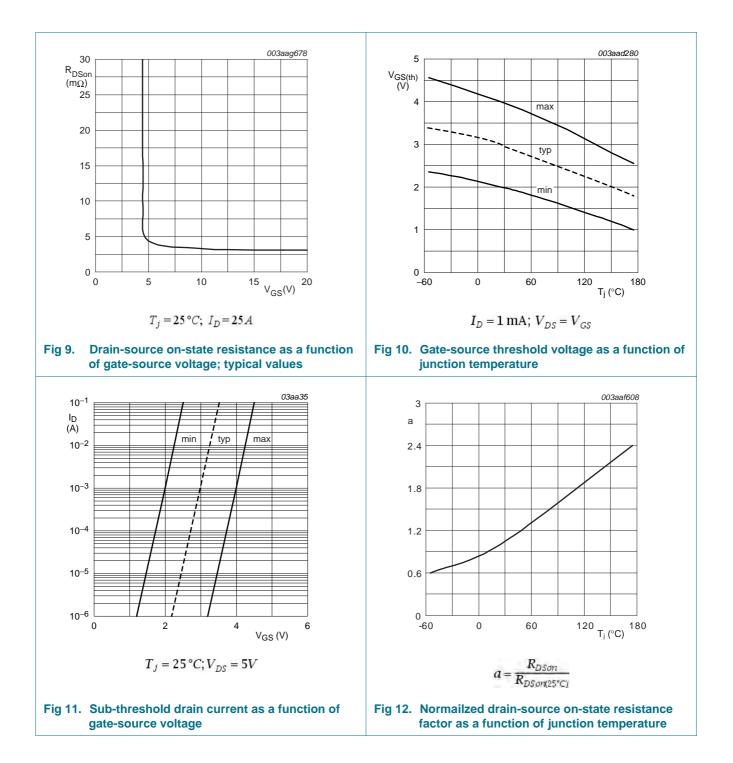
Conditions

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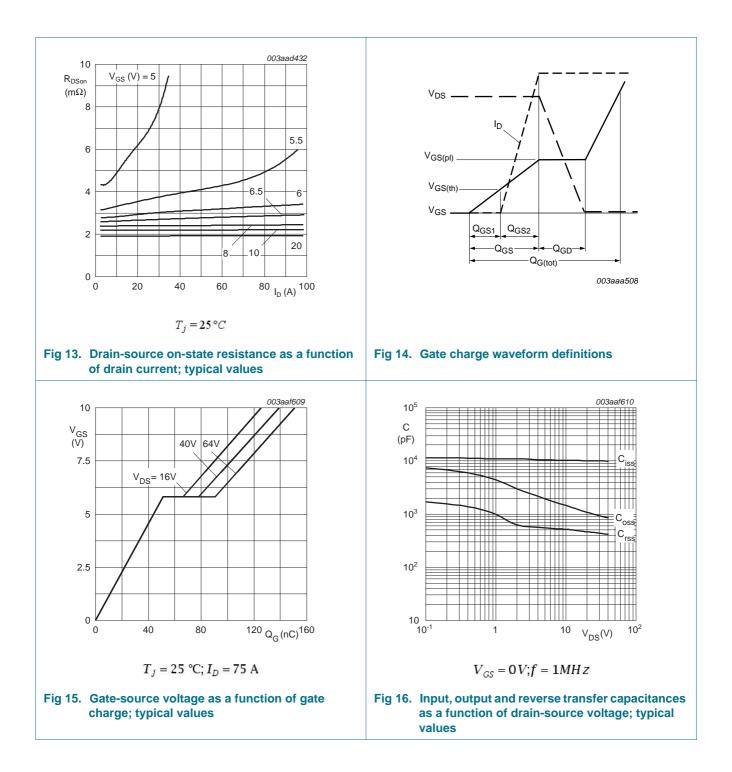


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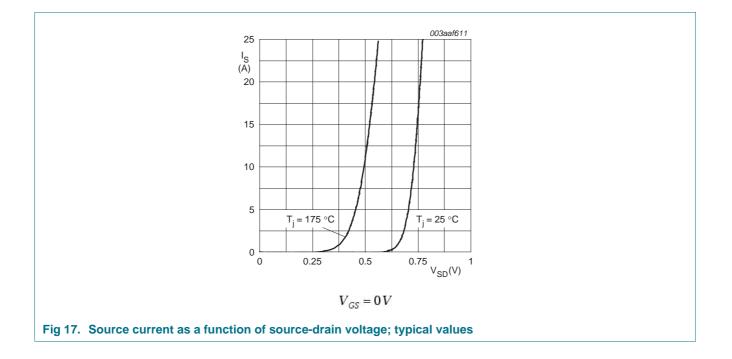


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7. Package outline

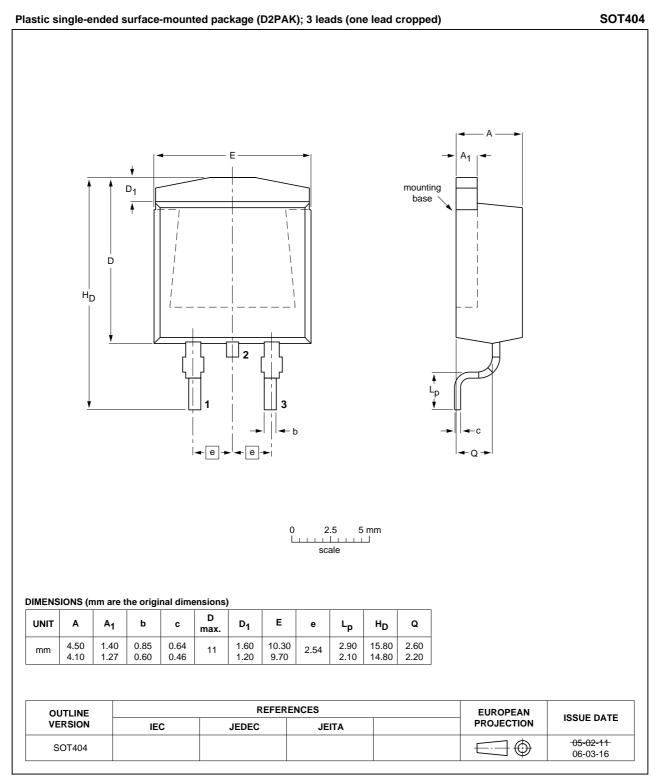


Fig 18. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7.Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN2R8-80BS v.2	20120229	Product data sheet	-	PSMN2R8-80BS v.1
Modifications:	 Status change 	d from objective to product.		
	 Various chang 	es to content.		
PSMN2R8-80BS v.1	20110928	Objective data sheet	-	-

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Product data sheet

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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